

# Q-band VCO based on Ku-band Oscillator and Q-band Multiplier

## GaAs Monolithic Microwave IC

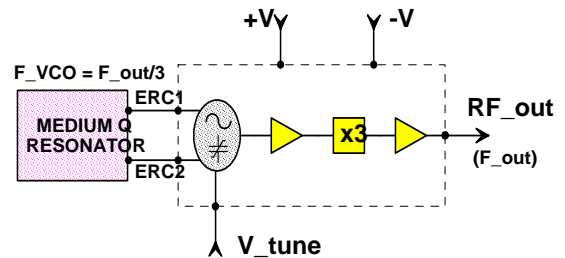
### Description

The CHV2242c is a monolithic multifunction for frequency generation. It integrates a Ku-band oscillator with frequency control (VCO), a Q-band frequency multiplier and buffer amplifiers. For performance optimisation, two external ports (ERC1 and ERC2) allow a passive resonator coupling to the oscillator (at one third of output frequency). On chip Schottky diode, based on a pHEMT, is used as varactor. All the active devices are internally self-biased.

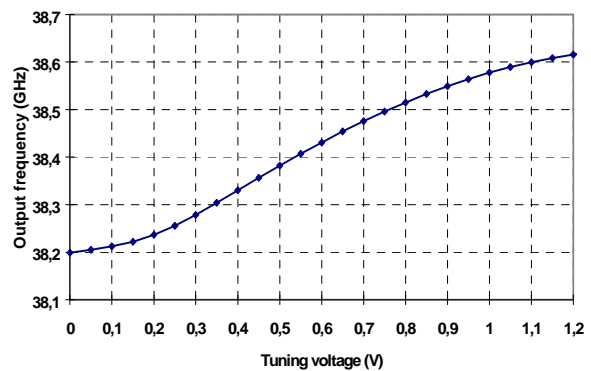
The circuit is manufactured with the pHEMT process 0.25µm gate length, via holes through the substrate, air bridges and electron beam gate lithography. It is available in chip form.

### Main Features

- Ku-band VCO + Q-band multiplier
- On chip varactor
- External resonator for centre frequency control and phase noise optimisation
- Low phase noise
- Auxiliary output at VCO frequency
- High temperature range
- On-chip self biasing
- Automatic assembly oriented
- Chip size 2.41 x 1.18 x 0.1mm
- BCB Layer protection



**Multifunction block diagram**



**Typical tuning characteristic**  
(Coupled to a micro-strip filter)

### Main Characteristics

Tamb = +25°C

| Symbol | Parameter                     | Min     | Typ   | Max  | Unit |
|--------|-------------------------------|---------|-------|------|------|
| F_out  | Output centre frequency       | 38      | 38.25 | 38.5 | GHz  |
| F_vco  | Oscillator frequency          | F_out/3 |       |      |      |
| F_tune | Output frequency tuning range | 150     | 200   |      | MHz  |
| Pout   | Output power                  | 5       | 7     |      | dBm  |

ESD Protections: Electrostatic discharge sensitive device observe handling precautions!

## Electrical Characteristics

Full temperature range, used according to section “Typical assembly and bias configuration”

| Symbol  | Parameter   | Min     | Typ                | Max               | Unit   |
|---------|---|---------|--------------------|-------------------|--------|
| F_out   | Output centre frequency   | 38      | 38.25              | 38.5              | GHz    |
| F_vco   | VCO frequency (1)   | F_out/3 |                    |                   |        |
| F_tune  | Frequency tuning range (at F_out) (2)                             | 150     | 200                |                   | MHz    |
| P_out   | Output power  | 5       | 7                  |                   | dBm    |
| F_slope | Frequency tuning slope (2)  |         | 500                |                   | MHz/V  |
| V_tune  | Control voltage range   |         | 0.2 – 0.8          | 0 – 1.5           | V      |
| Pushing | Frequency pushing vs positive supply voltage                      |         | 60                 |                   | MHz/v  |
| PN      | Phase noise (given at F_out) (2)<br>@ 10kHz<br>@ 100kHz<br>@ 1MHz |         | -48<br>-75<br>-100 | -43<br>-70<br>-95 | dBc/Hz |
| +V      | Positive supply voltage   | 4.4     | 4.5                | 4.6               | V      |
| +I      | Positive supply current   |         | 110                | 160               | mA     |
| -V      | Negative supply voltage   | -4.6    | -4.5               | -4.4              | V      |
| -I      | Negative supply current   |         | 5                  | 8                 | mA     |
| Top     | Operating temperature range                                       | -40     |                    | 100               | °C     |

(1) The centre frequency is given by the external passive resonator

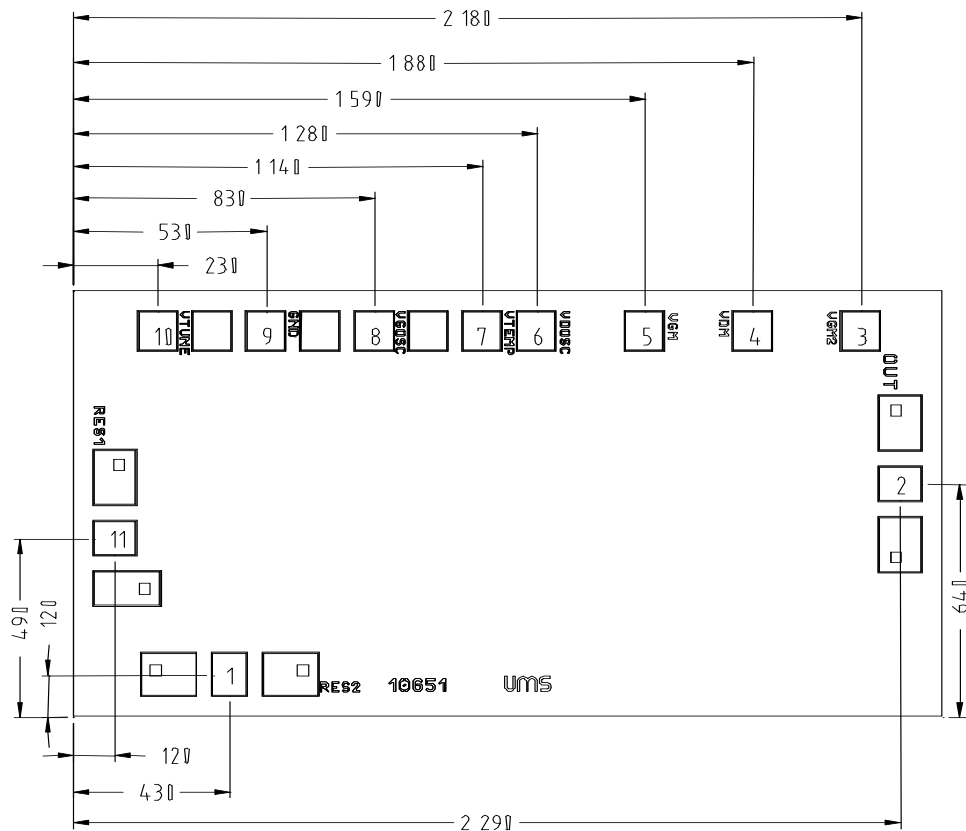
(2) This characteristic depends on the resonator Q, the given performance has been obtained by using a micro-strip filter used as resonator (see section “Proposed External Medium Q Resonator”)

## Absolute Maximum Ratings (1)

| Symbol | Parameter                 | Values      | Unit |
|--------|---------------------------|-------------|------|
| V_tune | Tuning voltage            | 2.5         | V    |
| +V     | Positive supply voltage   | 5           | V    |
| -V     | Negative supply voltage   | -5          | V    |
| +I     | Positive supply current   | 250         | mA   |
| -I     | Negative supply current   | 15          | mA   |
| Tstg   | Storage temperature range | -55 to +155 | °C   |

(1) Operation of this device above any one of these parameters may cause permanent damage.

## Chip Mechanical Data and Pin References



UNITS :  $\mu\text{m}$   
Tol :  $\pm 35\mu\text{m}$

Unit =  $\mu\text{m}$

External chip size = **2410 x 1180 +/- 35**

Chip thickness = 100 +/- 10

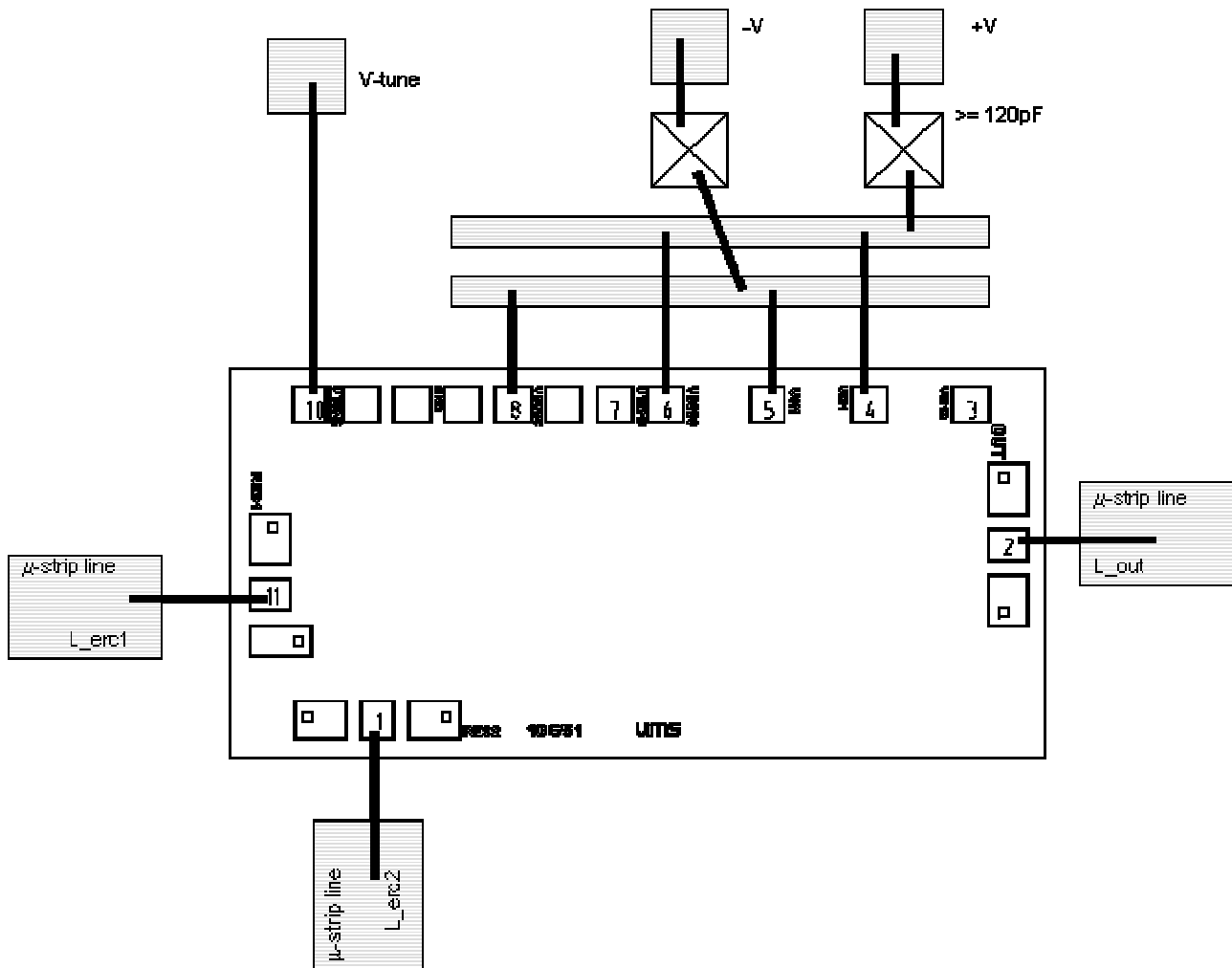
RF Pads (1, 2, 11) = **83 x 86**

DC/IF Pads = **98 x 95**

| Pin number       | Pin name      | Description  |
|------------------|---------------|--|
| <b>1</b>         | <b>ERC2</b>   | External Resonator Coupling Port 2   |
| <b>2</b>         | <b>RF_out</b> | RF output at 38GHz   |
| <b>3, 7</b>      |               | NC   |
| <b>4, 6</b>      | <b>+V</b>     | Positive supply voltage  |
| <b>5, 8</b>      | <b>-V</b>     | Negative supply voltage  |
| <b>9</b>         |               | GND (optional)   |
| <b>10</b>        | <b>V-tune</b> | Tuning voltage input port  |
| <b>11</b>        | <b>ERC1</b>   | External Resonator Coupling Port 1   |
| <b>No Number</b> |               | Ground : should not be bonded. If required, please ask for more information. |

Typical Assembly and Bias Configuration

DC and control lines



This drawing shows an example of assembly and bias configuration. All the transistors are internally self-biased. The positive and negative voltages can be respectively connected together (see drawing) according to the recommended values given in the electrical characteristics table. **Due to the high value of frequency sensitivity versus tuning voltage (around 500MHz/V), the signal applied to V\_tune port must have very low level of noise.**

For the RF pads the equivalent wire bonding inductance (diameter=25µm) has to be according to the following recommendation.

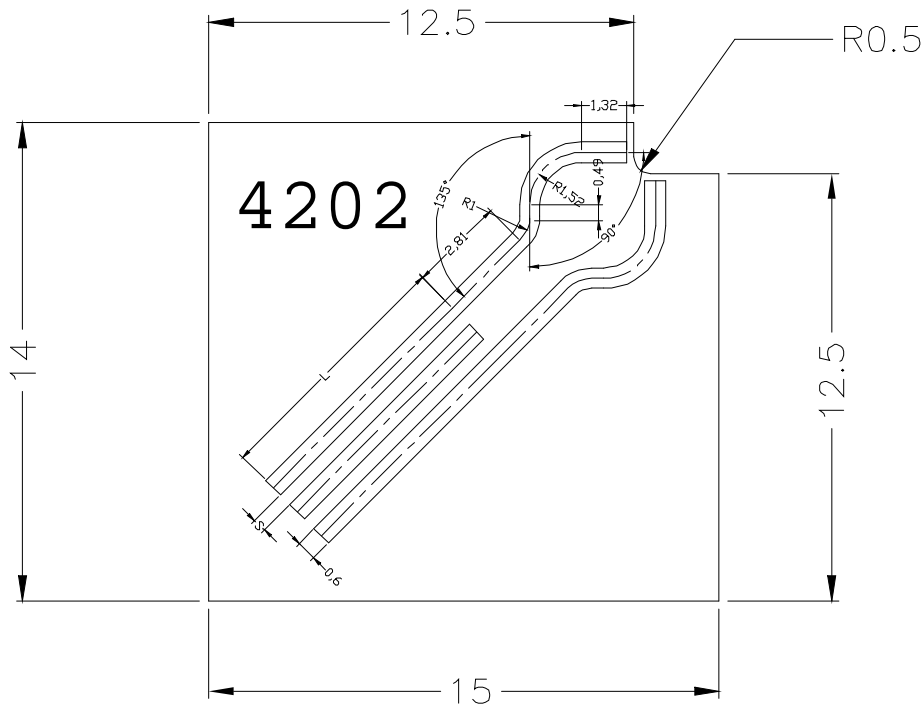
| Port       | Equivalent inductance (nH) | Approximated wire length (mm) |
|------------|----------------------------|-------------------------------|
| ERC1 (11)  | L_erc1 = 0.4               | 0.5                           |
| ERC2 (1)   | L_erc2 = 0.4               | 0.5                           |
| RF_out (2) | L_out = 0.28               | 0.35                          |

For a micro-strip configuration a hole in the substrate is recommended for chip assembly.

## Proposed External Medium Q Resonator

This resonator can be used for 77GHz FMCW-based radar applications.

The chip has been especially designed to be coupled to a medium Q resonator printed on temperature compensated soft substrate. The resonance is given by three half wave coupled lines. The length of the coupler (L) gives the centre frequency and the space between the coupled lines (s) gives the bandwidth. For easy connection and phase considerations half wave lines are at the input and output of the filter. All the recommended dimensions are given in the following drawing.



The main substrate characteristics are the following (ROGERS R03003)

| Dielectric constant | Thickness | Dissipation factor (10GHz) | Thermal coefficient |
|---------------------|-----------|----------------------------|---------------------|
| 3                   | 250µm     | 0.0013                     | 13 ppm/°C           |

The typical resonator length (L) is 7.35mm for a coupling value (s) of 0.4mm and for a frequency of 38.25GHz. However this L value should have to be adjusted depending on the final chip environment.

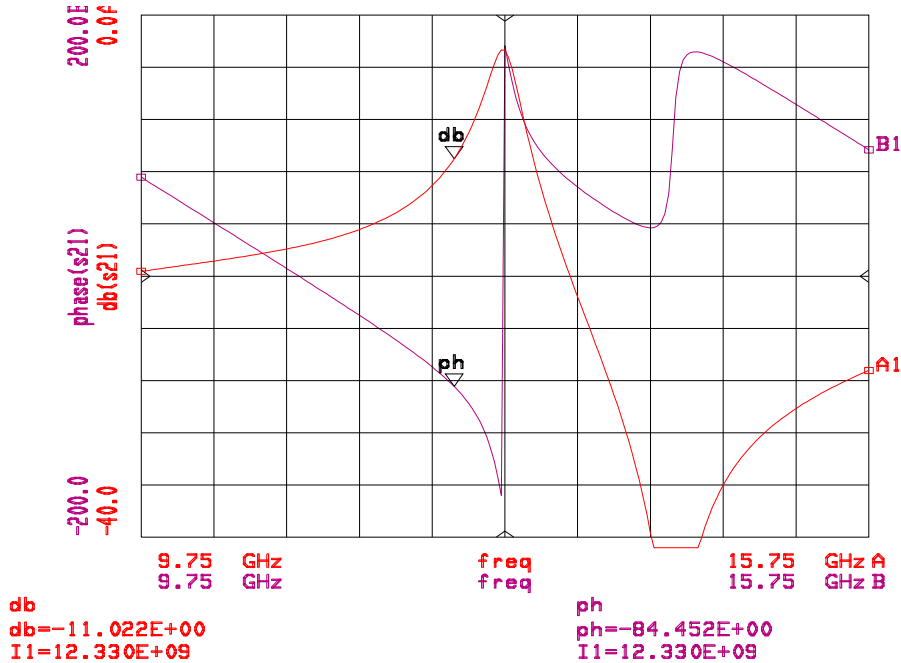
Other possibility is ARLON/CLTE substrate. (L is 7.27mm for s=0.4mm)

## Recommendation for Frequency stability

In order to ensure a good frequency stability (versus temperature, external resonator aging,...), it is recommended to use an external frequency locked loop with a low frequency loop filter (below modulation frequency), or a PLL for both frequency modulation and stability.

Proposed External Medium Q Resonator

The following information is about the S parameter of the resonator (plot for S21 and table for the four parameters). These values don't include the wire bonding equivalent inductance L\_erc1 and L\_erc2 given in section "Typical Assembly and Bias Configuration".



S21 of the proposed external resonator

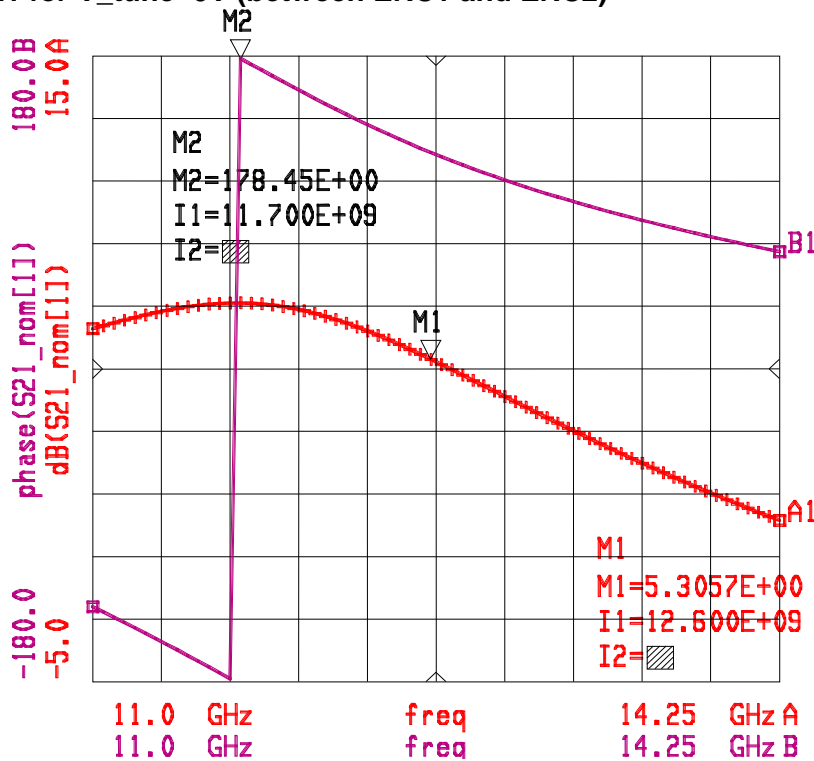
| freq      | dB(S11) | phase(S11) | dB(S21) | phase(S21) | dB(S12) | phase(S12) | dB(S22) | phase(S22) |
|-----------|---------|------------|---------|------------|---------|------------|---------|------------|
| 9.750E+09 | -0.269  | 165.984    | -19.639 | 75.748     | -19.639 | 75.748     | -0.269  | 165.984    |
| 10.05E+09 | -0.282  | 148.566    | -19.246 | 58.344     | -19.246 | 58.344     | -0.282  | 148.566    |
| 10.35E+09 | -0.294  | 131.116    | -18.849 | 40.900     | -18.849 | 40.900     | -0.294  | 131.116    |
| 10.65E+09 | -0.306  | 113.629    | -18.421 | 23.404     | -18.421 | 23.404     | -0.306  | 113.629    |
| 10.95E+09 | -0.320  | 96.082     | -17.921 | 5.819      | -17.921 | 5.819      | -0.320  | 96.082     |
| 11.25E+09 | -0.337  | 78.416     | -17.290 | -11.932    | -17.290 | -11.932    | -0.337  | 78.416     |
| 11.55E+09 | -0.364  | 60.508     | -16.428 | -30.016    | -16.428 | -30.016    | -0.364  | 60.508     |
| 11.85E+09 | -0.415  | 42.062     | -15.152 | -48.824    | -15.152 | -48.824    | -0.415  | 42.062     |
| 12.15E+09 | -0.543  | 22.219     | -13.061 | -69.511    | -13.061 | -69.511    | -0.543  | 22.219     |
| 12.45E+09 | -1.135  | -2.751     | -9.044  | -97.347    | -9.044  | -97.347    | -1.135  | -2.751     |
| 12.75E+09 | -12.026 | 15.650     | -2.717  | 176.749    | -2.717  | 176.749    | -12.026 | 15.650     |
| 13.05E+09 | -0.736  | -2.650     | -13.295 | 95.005     | -13.295 | 95.005     | -0.736  | -2.650     |
| 13.35E+09 | -0.357  | -27.461    | -21.583 | 68.175     | -21.583 | 68.175     | -0.357  | -27.461    |
| 13.65E+09 | -0.294  | -47.296    | -29.127 | 49.027     | -29.127 | 49.027     | -0.294  | -47.296    |
| 13.95E+09 | -0.278  | -65.784    | -39.725 | 36.983     | -39.725 | 36.983     | -0.278  | -65.784    |
| 14.25E+09 | -0.275  | -83.768    | -45.375 | 169.387    | -45.375 | 169.387    | -0.275  | -83.768    |
| 14.55E+09 | -0.277  | -101.542   | -35.988 | 164.157    | -35.988 | 164.157    | -0.277  | -101.542   |
| 14.85E+09 | -0.282  | -119.232   | -32.348 | 148.414    | -32.348 | 148.414    | -0.282  | -119.232   |
| 15.15E+09 | -0.289  | -136.894   | -30.136 | 131.474    | -30.136 | 131.474    | -0.289  | -136.894   |
| 15.45E+09 | -0.297  | -154.550   | -28.526 | 114.171    | -28.526 | 114.171    | -0.297  | -154.550   |
| 15.75E+09 | -0.305  | -172.202   | -27.227 | 96.721     | -27.227 | 96.721     | -0.305  | -172.202   |

S parameters of the proposed external resonator

**External Resonator Coupling Information**

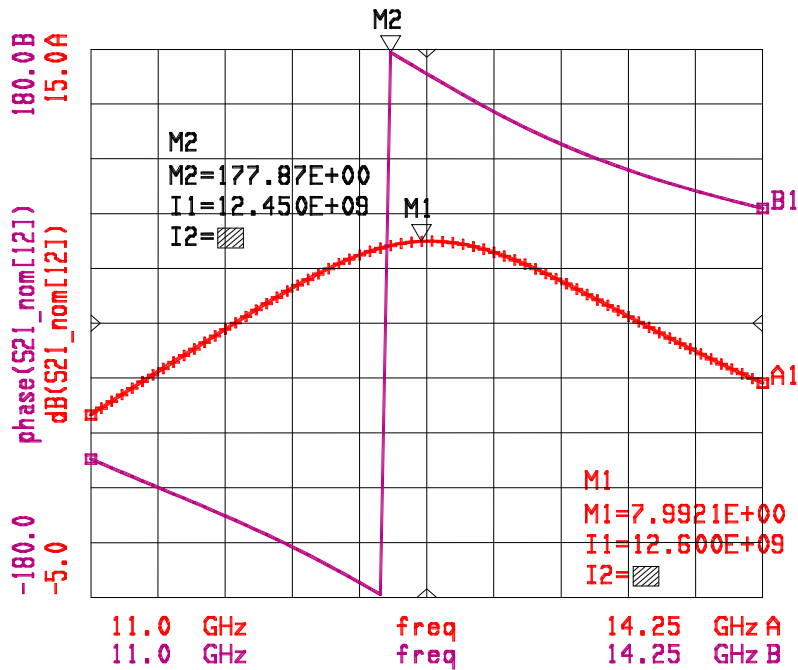
The external resonator has to be an equivalent band-pass filter with 180° insertion phase at resonance (oscillation) frequency. However, this filter must be compatible to the loop parameters of the oscillator (between ERC ports) in order to obtain the oscillation conditions and to avoid parasitic oscillations. The following information concerns the S parameters of the chip (plots for S21 and tables for the four parameters), reference ports are ERC1 and ERC2. These values don't include the wire bonding equivalent inductance L\_erc1 and L\_erc2 given in section "Typical Assembly and Bias Configuration". For more detail and for a wider band analysis a complete S parameter file is available on request.

**MMIC S21 for V\_tune=0V (between ERC1 and ERC2)**



| freq   | dB(S11) | Phase(S11) | dB(S21) | Phase(S21) | dB(S12) | Phase(S12) | dB(S22) | Phase(S22) |
|--------|---------|------------|---------|------------|---------|------------|---------|------------|
| 11     | -4.76   | -120.8     | 6.28    | -136.9     | -24.28  | 135.4      | -10.50  | -39.2      |
| 11.25  | -5.98   | -143.0     | 6.73    | -152.2     | -23.66  | 120.9      | -10.96  | -36.4      |
| 11.5   | -7.56   | -172.9     | 7.035   | -168.3     | -23.17  | 105.6      | -11.18  | -31.7      |
| 11.75  | -8.71   | 147.5      | 7.10    | 175.1      | -22.94  | 89.7       | -10.95  | -26.5      |
| 12     | -8.22   | 105.0      | 6.86    | 158.7      | -23.01  | 74.0       | -10.34  | -23.1      |
| 12.25  | -6.62   | 71.3       | 6.34    | 143.4      | -23.36  | 59.3       | -9.64   | -22.4      |
| 12.5   | -5.06   | 47.3       | 5.63    | 129.5      | -23.91  | 46.1       | -9.06   | -23.7      |
| 12.75  | -3.88   | 29.9       | 4.80    | 117.3      | -24.58  | 34.4       | -8.67   | -25.8      |
| 13     | -3.04   | 16.5       | 3.95    | 106.6      | -25.23  | 24.2       | -8.43   | -28.2      |
| 13.25  | -2.45   | 6.0        | 3.10    | 97.1       | -25.97  | 15.3       | -8.31   | -30.7      |
| 13.5   | -2.01   | -2.6       | 2.30    | 88.6       | -26.62  | 7.3        | -8.28   | -32.9      |
| 13.75  | -1.67   | -9.7       | 1.54    | 81.0       | -27.23  | 0.2        | -8.30   | -35.0      |
| 14     | -1.46   | -15.9      | 0.82    | 73.9       | -27.80  | -6.4       | -8.37   | -36.8      |
| 14..25 | -1.28   | -21.2      | 0.16    | 67.4       | -28.31  | -12.6      | -8.47   | -38.5      |

MMIC S21 for V\_tune=2V (between ERC1 and ERC2)



| freq   | dB(S11) | Phase(S11) | dB(S21) | Phase(S21) | dB(S12) | Phase(S12) | dB(S22) | Phase(S22) |
|--------|---------|------------|---------|------------|---------|------------|---------|------------|
| 11     | -6.2    | -16.0      | 1.66    | -89.1      | -28.9   | -176.9     | -9.16   | 50.9       |
| 11.25  | -5.2    | -34.1      | 2.88    | -103.6     | -27.5   | 169.5      | -9.86   | -52.7      |
| 11.5   | -5      | -50.3      | 4.07    | -117.8     | -26.1   | 156.0      | -10.82  | -53.7      |
| 11.75  | -5.5    | -66.5      | 5.26    | -132.6     | -24.8   | 142.0      | -12.14  | -52.6      |
| 12     | -7.1    | -84.5      | 6.39    | -148.6     | -23.5   | 126.6      | -13.76  | -46.1      |
| 12.25  | -10.4   | -107.1     | 7.34    | -166.6     | -22.4   | 109.4      | -14.75  | -30.0      |
| 12.5   | -18.4   | -151.9     | 7.91    | 173.9      | -21.6   | 90.4       | -13.45  | -12.4      |
| 12.75  | -16.1   | 80.0       | 7.94    | 153.9      | -21.4   | 71.1       | -11.18  | -6.7       |
| 13     | -9.1    | 45.0       | 7.46    | 135.3      | -21.8   | 53.0       | -9.42   | -9.6       |
| 13.25  | -5.8    | 25.9       | 6.63    | 119.1      | -22.4   | 37.3       | -8.39   | -15.0      |
| 13.5   | -4.1    | 11.9       | 5.66    | 105.4      | -23.3   | 24.1       | -7.87   | -20.6      |
| 13.75  | -3.0    | 1.2        | 4.66    | 93.9       | -24.1   | 13.1       | -7.64   | -25.5      |
| 14     | -2.3    | -7.5       | 3.7     | 84.1       | -24.9   | 3.7        | -7.59   | -29.6      |
| 14..25 | -1.9    | -14.5      | 2.81    | 75.5       | -25.7   | -4.5       | -7.64   | -33        |

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## Ordering Information

Chip form : CHV2242c98F/00

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